

Title (en)

METHOD FOR PRODUCING THE ELECTRICAL CONTACTS OF A SEMICONDUCTOR DEVICE

Title (de)

VERFAHREN ZUR HERSTELLUNG DER ELEKTRISCHEN KONTAKTE EINES HALBLEITERBAUELEMENTS

Title (fr)

PROCEDE DE REALISATION DE CONTACTS ELECTRIQUES D'UN DISPOSITIF SEMI-CONDUCTEUR

Publication

**EP 2888765 A2 20150701 (FR)**

Application

**EP 13756362 A 20130822**

Priority

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- EP 2013067443 W 20130822

Abstract (en)

[origin: WO2014029836A2] The invention relates to a method for producing an electrical contact (114) of a semiconductor device (100), said method comprising the following steps: depositing an electrically conductive and optically transparent layer (104) on a face (102) of the device; depositing first and second dielectric layers (106, 108) on the aforementioned layer, in which the second dielectric layer can be selectively engraved by laser; performing selective laser engraving on the second dielectric layer, such as to form a first opening; producing a second opening, aligned with the first opening, in the first dielectric layer; depositing an electrically conductive material on the electrically conductive and optically transparent layer through the second opening, such that portions of the electrically conductive material are deposited on the second dielectric layer around the first opening; engraving portions of the second dielectric layer that are not covered by the portions of electrically conductive material.

IPC 8 full level

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Citation (search report)

See references of WO 2014029836A2

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